Yasuo Takahashi

List of Publications by Year
in descending order

164	3,777	126907	155660
papers	citations	33 h-index	55 g-index

165	165	165	2251
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Three-dimensional siloxane resist for the formation of nanopatterns with minimum linewidth fluctuations. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 69.	1.6	248
2	Valley Polarization in Si(100) at Zero Magnetic Field. Physical Review Letters, 2006, 96, 236801.	7.8	131
3	Manipulation and detection of single electrons for future information processing. Journal of Applied Physics, 2005, 97, 031101.	2.5	112
4	Silicon single-electron devices. Journal of Physics Condensed Matter, 2002, 14, R995-R1033.	1.8	111
5	Single electron tunneling transistor with tunable barriers using silicon nanowire metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2006, 88, 053121.	3.3	111
6	A multiple-valued logic and memory with combined single-electron and metal-oxide-semiconductor transistors. IEEE Transactions on Electron Devices, 2003, 50, 462-470.	3.0	106
7	Multigate single-electron transistors and their application to an exclusive-OR gate. Applied Physics Letters, 2000, 76, 637-639.	3.3	98
8	Current quantization due to single-electron transfer in Si-wire charge-coupled devices. Applied Physics Letters, 2004, 84, 1323-1325.	3.3	94
9	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. Applied Physics Letters, 2007, 90, 102106.	3.3	90
10	Photoluminescence from a Silicon Quantum Well Formed on Separation by Implanted Oxygen Substrate. Japanese Journal of Applied Physics, 1995, 34, 950-954.	1.5	86
11	Si complementary single-electron inverter with voltage gain. Applied Physics Letters, 2000, 76, 3121-3123.	3.3	84
12	Mechanism of Potential Profile Formation in Silicon Single-Electron Transistors Fabricated Using Pattern-Dependent Oxidation. Japanese Journal of Applied Physics, 2001, 40, L29-L32.	1.5	80
13	Manipulation of elementary charge in a silicon charge-coupled device. Nature, 2001, 410, 560-562.	27.8	77
14	In situ transmission electron microscopy analysis of conductive filament during solid electrolyte resistance switching. Applied Physics Letters, 2011, 98, .	3.3	76
15	Excellent charge offset stability in a Si-based single-electron tunneling transistor. Applied Physics Letters, 2001, 79, 3188-3190.	3.3	73
16	Self-diffusion of Si in thermally grown SiO2 under equilibrium conditions. Journal of Applied Physics, 2003, 93, 3674-3676.	2.5	68
17	Modeling of Si self-diffusion in SiO2: Effect of the Si/SiO2 interface including time-dependent diffusivity. Applied Physics Letters, 2004, 84, 876-878.	3.3	67
18	Room-temperature-operating data processing circuit based on single-electron transfer and detection with metal-oxide-semiconductor field-effect transistor technology. Applied Physics Letters, 2006, 88, 183101.	3.3	64

#	Article	IF	Citations
19	Timeâ€resolved measurement of singleâ€electron tunneling in a Si singleâ€electron transistor with satellite Si islands. Applied Physics Letters, 1995, 67, 2957-2959.	3.3	63
20	Switching operation and degradation of resistive random access memory composed of tungsten oxide and copper investigated using in-situ TEM. Scientific Reports, 2015, 5, 17103.	3.3	60
21	Electron pump by a combined single-electron/field-effect- transistor structure. Applied Physics Letters, 2003, 82, 1221-1223.	3.3	59
22	Effect of the Si/SiO2 interface on self-diffusion of Si in semiconductor-grade SiO2. Applied Physics Letters, 2003, 83, 3897-3899.	3.3	55
23	Thermal Agglomeration of Thin Single Crystal Si on $f SiO_{2}$ in Vacuum. Japanese Journal of Applied Physics, 1995, 34, 1728-1735.	1.5	54
24	Observation of Single Electron-Hole Recombination and Photon-Pumped Current in an Asymmetric Si Single-Electron Transistor. Physical Review Letters, 1997, 78, 1532-1535.	7.8	50
25	Multipeak negative-differential-resistance device by combining single-electron and metalâ€“oxideâ€“semiconductor transistors. Applied Physics Letters, 2001, 79, 3618-3620.	3.3	49
26	Counterâ€oxidation of superficial Si in singleâ€crystalline Si on SiO2structure. Applied Physics Letters, 1994, 65, 2987-2989.	3.3	48
27	Double-island single-electron devices. A useful unit device for single-electron logic LSI's. IEEE Transactions on Electron Devices, 1999, 46, 954-959.	3.0	48
28	Selective Ge deposition on Si using thermal decomposition of GeH4. Applied Physics Letters, 1985, 47, 863-865.	3.3	47
29	Germanium Atomic Layer Epitaxy Controlled by Surface Chemical Reactions. Journal of the Electrochemical Society, 1989, 136, 1826-1827.	2.9	46
30	Designing of silicon effective quantum dots by using the oxidation-induced strain: a theoretical approach. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 337-341.	2.7	43
31	Why the long-term charge offset drift in Si single-electron tunneling transistors is much smaller (better) than in metal-based ones: Two-level fluctuator stability. Journal of Applied Physics, 2008, 104, .	2.5	43
32	Filament formation and erasure in molybdenum oxide during resistive switching cycles. Applied Physics Letters, 2014, 105, .	3.3	41
33	Suppression of Effects of Parasitic Metal-Oxide-Semiconductor Field-Effect Transistors on Si Single-Electron Transistors. Japanese Journal of Applied Physics, 1998, 37, 3257-3263.	1.5	36
34	Self-Limiting Adsorption of SiCl2H2and Its Application to the Layer-by-Layer Photochemical Process. Japanese Journal of Applied Physics, 1991, 30, L209-L211.	1.5	35
35	Fabrication of thickness-controlled silicon nanowires and their characteristics. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2166.	1.6	34
36	Charge offset stability in tunable-barrier Si single-electron tunneling devices. Applied Physics Letters, 2007, 90, 033507.	3.3	34

#	Article	IF	Citations
37	Silicon single-electron devices. International Journal of Electronics, 1999, 86, 605-639.	1.4	32
38	Multilevel memory using an electrically formed single-electron box. Applied Physics Letters, 2004, 85, 1277-1279.	3.3	31
39	Detection of single charges and their generation-recombination dynamics in Si nanowires at room temperature. Applied Physics Letters, 2002, 80, 4567-4569.	3.3	30
40	Error mechanisms and rates in tunable-barrier single-electron turnstiles and charge-coupled devices. Journal of Applied Physics, 2004, 96, 5254-5266.	2.5	30
41	Energy Eigenvalues and Quantized Conductance Values of Electrons in Si Quantum Wires on mb{100mb} Plane. Japanese Journal of Applied Physics, 1995, 34, 5489-5498.	1.5	29
42	Evidence for activated conduction in a single electron transistor. Journal of Applied Physics, 2001, 89, 410-419.	2.5	28
43	Probing electrochemistry at the nanoscale: in situ TEM and STM characterizations of conducting filaments in memristive devices. Journal of Electroceramics, 2017, 39, 73-93.	2.0	28
44	Quantized Conductance of a Silicon Wire Fabricated by Separation-by-Implanted-Oxygen Technology. Japanese Journal of Applied Physics, 1995, 34, 1309-1314.	1.5	26
45	A Merged Single-Electron Transistor and Metal-Oxide-Semiconductor Transistor Logic for Interface and Multiple-Valued Functions. Japanese Journal of Applied Physics, 2002, 41, 2566-2568.	1.5	25
46	I-V measurement of NiO nanoregion during observation by transmission electron microscopy. Journal of Applied Physics, 2011, 109, 053702.	2.5	25
47	Turnstile Operation Using a Silicon Dual-Gate Single-Electron Transistor. Japanese Journal of Applied Physics, 2003, 42, L1109-L1111.	1.5	24
48	Silicon Single-Electron Devices. Nanostructure Science and Technology, 2009, , 125-172.	0.1	23
49	Ge Atomic Layer Epitaxy by Use of Ar Ion Laser Heating. Japanese Journal of Applied Physics, 1989, 28, 2387-2390.	1.5	22
50	In-situ transmission electron microscopy of conductive filaments in NiO resistance random access memory and its analysis. Journal of Applied Physics, 2013, 113, 083701.	2.5	22
51	Development of TEM Holder Generating In-Plane Magnetic Field Used for <i>In-Situ</i> TEM Observation. Materials Transactions, 2014, 55, 403-409.	1.2	22
52	Smooth Interfacial Scavenging for Resistive Switching Oxide via the Formation of Highly Uniform Layers of Amorphous TaO_x. ACS Applied Materials & Interfaces, 2018, 10, 5609-5617.	8.0	22
53	A Si Memory Device Composed of a One-Dimensional Metal-Oxide-Semiconductor Field-Effect-Transistor Switch and a Single-Electron-Transistor Detector. Japanese Journal of Applied Physics, 1999, 38, 2457-2461.	1.5	20
54	Single-electron and quantum SOI devices. Microelectronic Engineering, 2001, 59, 435-442.	2.4	20

#	Article	IF	Citations
55	Threshold Voltage of Si Single-Electron Transistor. Japanese Journal of Applied Physics, 2003, 42, 2429-2433.	1.5	20
56	Preparation of resistance random access memory samples for in situ transmission electron microscopy experiments. Thin Solid Films, 2013, 533, 48-53.	1.8	20
57	Correlated diffusion of silicon and boron in thermally grown SiO2. Applied Physics Letters, 2004, 85, 221-223.	3.3	19
58	Analysis of resistance switching and conductive filaments inside Cu-Ge-S using in situ transmission electron microscopy. Journal of Materials Research, 2012, 27, 886-896.	2.6	19
59	Observation and Circuit Application of Negative Differential Conductance in Silicon Single-Electron Transistors. Japanese Journal of Applied Physics, 2002, 41, 2569-2573.	1.5	18
60	Analysis of Back-Gate Voltage Dependence of Threshold Voltage of Thin Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor and Its Application to Si Single-Electron Transistor. Japanese Journal of Applied Physics, 2004, 43, 2036-2040.	1.5	18
61	Fabrication ofSiO2/Si/SiO2Double Barrier Diodes using Two-Dimensional Si Structures. Japanese Journal of Applied Physics, 1997, 36, 3669-3674.	1.5	17
62	Infrared detection with silicon nano-field-effect transistors. Applied Physics Letters, 2007, 90, 223108.	3.3	17
63	Switching of Cu/MoO_x/TiN CBRAM at MoO_x/TiN interface. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 306-310.	1.8	17
64	Microstructural transitions in resistive random access memory composed of molybdenum oxide with copper during switching cycles. Nanoscale, 2016, 8, 14754-14766.	5.6	17
65	Single-Electron Transistor and Current-Switching Device Fabricated by Vertical Pattern-Dependent Oxidation. Japanese Journal of Applied Physics, 2000, 39, 2325-2328.	1.5	16
66	Multifunctional Device Using Nanodot Array. Japanese Journal of Applied Physics, 2006, 45, 5317-5321.	1.5	16
67	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and295K. Physical Review B, 2006, 74, .	3.2	15
68	The Observation of â€œConduction Spotâ€•on NiO Resistance Random Access Memory. Japanese Journal of Applied Physics, 2011, 50, 081101.	1.5	15
69	Transport properties of silicon nanostructures fabricated on SIMOX substrates. Microelectronic Engineering, 1995, 28, 399-405.	2.4	14
70	Silicon nanodisk array with a fin field-effect transistor for time-domain weighted sum calculation toward massively parallel spiking neural networks. Applied Physics Express, 2016, 9, 034201.	2.4	14
71	Mechanism of Single-Charge Detection using Electronâ€“Hole System in Si-wire Transistors. Japanese Journal of Applied Physics, 2002, 41, 1209-1213.	1.5	13
72	Single-electron devices formed by pattern-dependent oxidation: microscopic structural evaluation. Applied Surface Science, 2002, 190, 144-150.	6.1	13

#	Article	IF	Citations
73	Effect of Si/SiO2Interface on Silicon and Boron Diffusion in Thermally Grown SiO2. Japanese Journal of Applied Physics, 2004, 43, 7837-7842.	1.5	13
74	Electrostatically gated Si devices: Coulomb blockade and barrier capacitance. Applied Physics Letters, 2006, 89, 052102.	3.3	13
75	Single-Electron Device With Si Nanodot Array and Multiple Input Gates. IEEE Nanotechnology Magazine, 2009, 8, 535-541.	2.0	13
76	Growth and Etching of Germanium Films by Chemical Vapor Deposition in a GeCl4â€‰â€â€‰â€‰Hâ€‰2 Gas System. Journal of the Electrochemical Society, 1988, 135, 1539-1543.	2.9	11
77	Co-tunneling current in very small Si single-electron transistors. Physica B: Condensed Matter, 1996, 227, 105-108.	2.7	11
78	Electron tunneling from the edge of thin singleâ€crystal Si layers through SiO2film. Journal of Applied Physics, 1996, 80, 4450-4457.	2.5	11
79	Sub-10-nm Overlay Accuracy in Electron Beam Lithography for Nanometer-Scale Device Fabrication. Japanese Journal of Applied Physics, 1998, 37, 6788-6791.	1.5	11
80	Theory of activated conduction in a Si single-electron transistor. Microelectronic Engineering, 1999, 47, 205-207.	2.4	11
81	The Effect of Partial Pressure of Oxygen on Self-Diffusion of Si in SiO2. Japanese Journal of Applied Physics, 2003, 42, L1492-L1494.	1.5	11
82	Simulation of correlated diffusion of Si and B in thermally grown SiO2. Journal of Applied Physics, 2004, 96, 5513-5519.	2.5	11
83	In situConductance Measurement of a Limited Number of Nanoparticles during Transmission Electron Microscopy Observation. Japanese Journal of Applied Physics, 2005, 44, L790-L792.	1.5	11
84	Intersubband Scattering in Double-Gate MOSFETs. IEEE Nanotechnology Magazine, 2006, 5, 430-435.	2.0	10
85	The Observation of â€œConduction Spotâ€•on NiO Resistance Random Access Memory. Japanese Journal of Applied Physics, 2011, 50, 081101.	1.5	10
86	Voltage Gain of Si Single-Electron Transistor and Analysis of Performance of n-Metal-Oxide-Semiconductor Type Inverter with Resistive Load. Japanese Journal of Applied Physics, 2002, 41, 458-463.	1.5	9
87	Fabrication of single-electron transistors and circuits using SOIs. Solid-State Electronics, 2002, 46, 1723-1727.	1.4	9
88	Charge-State Control of Phosphorus Donors in Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2005, 44, 2588-2591.	1.5	9
89	New platinum silicide formation method using reaction between platinum and silane. Journal of Applied Physics, 1985, 58, 3190-3194.	2.5	8
90	Quantized conductance in a small one-dimensional Si wire on a thin silicon-on-insulator substrate fabricated using SiN-film-masked oxidation. Semiconductor Science and Technology, 1998, 13, 1047-1051.	2.0	8

#	Article	IF	Citations
91	Simultaneous-Sweep Method for Evaluation of Single-Electron Transistors with Barriers Induced by Gate Electric Field. Japanese Journal of Applied Physics, 2004, 43, L1048-L1050.	1.5	8
92	Automatic Control of Oscillation Phase of a Single-Electron Transistor. IEEE Electron Device Letters, 2004, 25, 31-33.	3.9	8
93	Back-Gate Effect on Coulomb Blockade in Silicon-on-Insulator Trench Wires. Japanese Journal of Applied Physics, 2005, 44, 7717-7719.	1.5	8
94	Silicon epitaxial growth on germanium using an Si2H6 low-pressure chemical vapor deposition technique. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 225.	1.6	7
95	Si memory device operated with a small number of electrons by using a single-electron-transistor detector. Electronics Letters, 1998, 34, 45.	1.0	7
96	Development of silicon single-electron devices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 95-101.	2.7	7
97	Tunnel current measurement of MgO and MgO/Fe/MgO nanoregions during TEM observation. Superlattices and Microstructures, 2008, 44, 633-640.	3.1	7
98	Fabrication of double-dot single-electron transistor in silicon nanowire. Thin Solid Films, 2010, 518, S186-S189.	1.8	7
99	Periodic Coulomb blockade oscillations observed in single-layered Fe nanodot array. Thin Solid Films, 2020, 704, 138012.	1.8	7
100	Stable and Tunable Current-Induced Phase Transition in Epitaxial Thin Films of Ca2RuO4. ACS Applied Materials & Interfaces, 2020, 12, 28368-28374.	8.0	7
101	Microscopic Observations of Single-Electron Island in Si Single-Electron Transistors. Japanese Journal of Applied Physics, 2003, 42, 2438-2443.	1.5	6
102	Long Retention of Gain-Cell Dynamic Random Access Memory With Undoped Memory Node. IEEE Electron Device Letters, 2007, 28, 48-50.	3.9	6
103	Charge transport in boron-doped nano MOSFETs: Towards single-dopant electronics. Applied Surface Science, 2008, 254, 6252-6256.	6.1	6
104	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. Journal of Applied Physics, 2015, 118, .	2.5	6
105	Fabrication and evaluation of series-triple quantum dots by thermal oxidation of silicon nanowire. AIP Advances, 2015, 5, .	1.3	6
106	Coupling capacitance between double quantum dots tunable by the number of electrons in Si quantum dots. Journal of Applied Physics, 2015, 117, .	2.5	6
107	Visualization of Conductive Filament during Write and Erase Cycles on Nanometer-Scale ReRAM Achieved by In-Situ TEM. , 2015, , .		6
108	Spike-based time-domain weighted-sum calculation using nanodevices for low power operation. , 2016, , .		6

#	Article	IF	Citations
109	Ultrahigh-Frequency Characteristics of Single-Electron Transistor. , 2018, , .		6
110	Silicon epitaxy on germanium using a SiH4 low-pressure chemical-vapor deposition process. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1551.	1.6	5
111	Measurements of Diffusion Coefficiens of Water in Electron Cryclotron Resonance Plasma SiO2. Japanese Journal of Applied Physics, 1993, 32, L431-L433.	1.5	5
112	A silicon bi-layer system. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 72-75.	2.7	5
113	Silicon nanodot-array device with multiple gates. Materials Science in Semiconductor Processing, 2008, 11, 175-178.	4.0	5
114	Electron aspirator using electronâ€“electron scattering in nanoscale silicon. Nature Communications, 2018, 9, 4813.	12.8	5
115	Asymmetric tunnel barrier in a Si single-electron transistor. Microelectronic Engineering, 1999, 47, 197-199.	2.4	4
116	Conductance measurements of nanoscale regions with in situ transmission electron microscopy. Materials Science and Engineering C, 2006, 26, 776-781.	7.3	4
117	Initial states and analog switching behaviors of two major tantalum oxide resistive memories. Japanese Journal of Applied Physics, 2020, 59, 044004.	1.5	4
118	Charge-offset stability of single-electron devices based on single-layered Fe nanodot array. AIP Advances, 2021, 11, .	1.3	4
119	Surface Photochemical Reactions of Dimethylgermane, Geâ€‰(â€‰â€‰CHâ€‰3â€‰)â€‰2â€‰Hâ€‰2, and Their Application to Ge Growth. Journal of the Electrochemical Society, 1995, 142, 1952-1956.	2.9	3
120	Single-electron device using Si nanodot array and multi-input gates. , 2006, , .		3
121	Filamentary switching of ReRAM investigated by in-situ TEM. Japanese Journal of Applied Physics, 2020, 59, SG0803.	1.5	3
122	Observation of shot noise suppression at the peaks of Coulomb oscillations. Solid-State Electronics, 1998, 42, 1429-1431.	1.4	2
123	Real-Time Observation of Single-Electron Movement through Silicon Single-Electron Transistor. Japanese Journal of Applied Physics, 2004, 43, 6863-6867.	1.5	2
124	Silicon single-charge transfer devices. Journal of Physics and Chemistry of Solids, 2008, 69, 702-707.	4.0	2
125	Effect of Arrangement of Input Gates on Logic Switching Characteristics of Nanodot Array Device. IEICE Transactions on Electronics, 2012, E95.C, 865-870.	0.6	2
126	In Situ Transmission Electron Microscopy for Electronics. , 0, , .		2

#	Article	IF	Citations
127	Capacitance evaluation of compact silicon triple quantum dots by simultaneous gate voltage sweeping. Journal of Applied Physics, 2016, 120, 234502.	2.5	2
128	Analog memory characteristics of 1T1R MoOx resistive random access memory. , 2016, , .		2
129	Oxygen Distribution around Filament in Ta-O Resistive RAM Fabricated Using 40 nm CMOS Technology. , 2018, , .		2
130	Tunnel magnetocapacitance in Fe/MgF2 single nanogranular layered films. Applied Physics Letters, 2020, 116, .	3.3	2
131	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. International Journal of Nanotechnology and Molecular Computation, 2009, 1, 58-69.	0.3	2
132	Silicon Single-Electron Pump and Turnstile: Interplay with Crystalline Imperfections. Materials Research Society Symposia Proceedings, 2005, 864, 671.	0.1	1
133	Tunnel Conductance through One or a Few Fe Particles Embedded in an MgO Matrix. Japanese Journal of Applied Physics, 2006, 45, 1946-1949.	1.5	1
134	High-frequency properties of Si single-electron transistor. , 2012, , .		1
135	Real-time resistive switching of Cu/MoOx ReRAM observed in transmission electron microscope. , 2014, , .		1
136	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO3/Pt. MRS Advances, 2018, 3, 1925-1930.	0.9	1
137	Controlled Current Transport in Pt/Nb:SrTiO₃ Junctions via Insertion of Uniform Thin Layers of TaO_x. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900136.	2.4	1
138	Si Electron Nano-Aspirator towards Emerging Hydro-Electronics. , 2019, , .		1
139	Initial electrical properties of tantalum oxide resistive memories influenced by oxygen defect concentrations. Japanese Journal of Applied Physics, 2021, 60, SCCE03.	1.5	1
140	In-situ TEM of Nanoscale ReRAM Devices. Vacuum and Surface Science, 2018, 61, 766-771.	0.1	1
141	Surface reactions of Ge chemical vapor deposition using diethylgermane. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1997, 15, 439-442.	2.1	0
142	Silicon Single-Electron Transistors and Single-Electron CCD. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
143	RESISTANCE SPIKES INDUCED BY GATE-CONTROLLED VALLEY-SPLITTING IN SILICON. International Journal of Modern Physics B, 2004, 18, 3603-3608.	2.0	0
144	Silicon-Based, Tunable-Barrier Single Charge Sources. , 2004, , .		0

#	Article	IF	Citations
145	Full adder operation based on Si nanodot array device. , 2008, , .		0
146	Si Nanodot Device Fabricated by Thermal Oxidation and their Applications. Key Engineering Materials, 2011, 470, 175-183.	0.4	0
147	In-Situ Transmission Electron Microscopy Observation of Electromigration in Au Thin Wires. Journal of Nanoscience and Nanotechnology, 2012, 12, 8741-8745.	0.9	0
148	Multifunctional Logic Gate by Means of Nanodot Array with Different Arrangements. Journal of Nanomaterials, 2013, 2013, 1-7.	2.7	0
149	Highly functional three-terminal nanodot array device with almost independent input gates. , 2014, , .		0
150	Tunable coupling capacitance of double-quantum-dot single-electron transistor with multiple gates. , 2014, , .		0
151	In-situ TEM observation of ReRAM switching. , 2014, , .		0
152	Evaluation of the origin of excited states appeared in small Si single-electron transistors. , 2016, , .		0
153	Evaluation of multilevel memory capability of ReRAM using Ta<inf>2</inf>O<inf>5</inf> insulator and different electrode materials. , 2017, , .		0
154	Associative search using pseudo-analog memristors. , 2017, , .		0
155	Detection of single holes generated by impact ionization in silicon. Applied Physics Letters, 2018, 113, 163103.	3.3	0
156	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO3/Pt â€“ CORRIGENDUM. MRS Advances, 2018, 3, 2075-2075.	0.9	0
157	Nanoscale Switching and Degradation of Resistive Random Access Memory Studied by In Situ Electron Microscopy. , 0, , .		0
158	Double-gate single-electron devices formed by single-layered Fe nanodot array. , 2020, , .		0
159	Initialization process of Cu-based WO_x conductive bridge RAM investigated via in situ transmission electron microscopy. Japanese Journal of Applied Physics, 2020, 59, SIIE01.	1.5	0
160	Probing Electrochemistry at the Nanoscale: In Situ TEM and STM Characterizations of Conducting Filaments in Memristive Devices. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 87-120.	0.5	0
161	<I>In situ</I> Transmission Electron Microscopy on the Conductance Quantization of a Fe Nano-particle System. Materia Japan, 2005, 44, 990-990.	0.1	0
162	Investigation on Switching Operation in Resistive RAM Using In-Situ TEM. Springer Proceedings in Physics, 2017, , 205-214.	0.2	0

#	Article	IF	Citations
163	Single-Electron Logic Devices. , 2017, , 281-304.		0
164	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. , 0, , 131-139.		0